

IN THE CLAIMS:

11. (Original) A process of manufacturing a semiconductor device, comprising:
- forming a first insulating film;
 - removing a selected portion of the first insulating film, thereby forming an opening;
 - forming a capacitor at a selected position in the opening;
 - forming a second insulating film at least in the opening; and
 - forming a third insulating film on the second insulating film.
12. (Original) The process of manufacturing a semiconductor device according to claim 11, further comprising forming a diffusion preventing film on which the first insulating film is formed.
13. (Original) The process of manufacturing a semiconductor device according to claim 11, further comprising forming a diffusion preventing film between the capacitor and the second insulating film.
14. (Original) The process of manufacturing a semiconductor device according to claim 11, further comprising: forming a first diffusion preventing film on which the first insulating film is formed; and forming a second diffusion preventing film between the capacitor and the second insulating film.

15. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the first insulating film is one of a low dielectric film, a diffusion preventing film and a laminated film formed of the low dielectric film and the diffusion preventing film.

16. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the third insulating film is a low dielectric film, and the second insulating film comprises a relative dielectric constant higher than the third insulating film.

17. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the second insulating film is a coated organic insulating film.

18. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the capacitor is thinner than the first insulating film.

19. (Original) The process of manufacturing a semiconductor device according to claim 11, wherein the second insulating film is formed only in the opening.

20. (Original) The process of manufacturing a semiconductor, device according to claim 11, further comprising:
forming the second insulating film on the first insulating film and the capacitor;
and

flattening the second insulating film by CMP until a surface of the first insulating film is exposed.

Please cancel claims 1 to 10 without prejudice, admission, surrender or any intention to create any estoppel as to equivalents.